

R820T

High Performance Low Power Advanced Digital TV Silicon Tuner Datasheet



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R820T

High Performance Low Power Advanced Digital TV Silicon Tuner

General Description

In heritage from Rafael Micro's state-of-the-art architecture, the R820T digital silicon tuner achieves the lowest power consumption and the smallest form factor. R820T offers unmatched RF performance for all digital broadcast television standards including DVB-T, ATSC, DMB-T, ISDB-T. With innovative AccuTune™ and TrueRF™ mechanisms, R820T provides superior performance in sensitivity, linearity, adjacent channel immunity, and image rejection. The chip embeds a smart power detector to optimize different input power scenarios as well as the spurious free dynamic range.

The R820T is a highly integrated silicon tuner that builds in low noise amplifier (LNA), mixer, fractional PLL, VGA, voltage regulator and tracking filter, eliminating the need for external SAW filters, LNA, balun, and LDO. Thanks to the LNA architecture, R820T offers the lowest cost and high performance solution for digital TV application. On-chip LDO, high performance LNA, and small package enable R820T the perfect solution for both cost and form factor sensitive applications.

With proprietary GreenRF techniques, R820T achieves both high performance and the lowest power consumption which perfectly complies with the worldwide trend. The R820T

comes in a small and thin QFN RoHS compliant package.

Features

- Support all digital TV standards: DVB-T, ATSC, DTMB and ISDB-T.
- Lowest BOM cost WITHOUT external SAW filters, LNA, balun, LDO, and adjustable parts.
- Low cost Single-In Digital TV Application
- Compliant with EN 300 744, NORDIG 2.2, D-BOOK 7.0, ARIB B21, ABNT 15604, ATSC A74 and GB20600-2006
- Compliant with EN-55020, EN55013 and FCC
- Ultra low power consumption < 178mA
- Single power supply 3.3V
- 2-wired I2C interface
- 24-pin 4x4 QFN lead-free package

Applications

- Terrestrial Digital TV
- Desktop/Laptop PCTV, Mini-card, and USB peripherals
- Set Top Box
- Portable Media Player
- Automobile TV

Figure A: Example of DTV reception for PCTV Applications

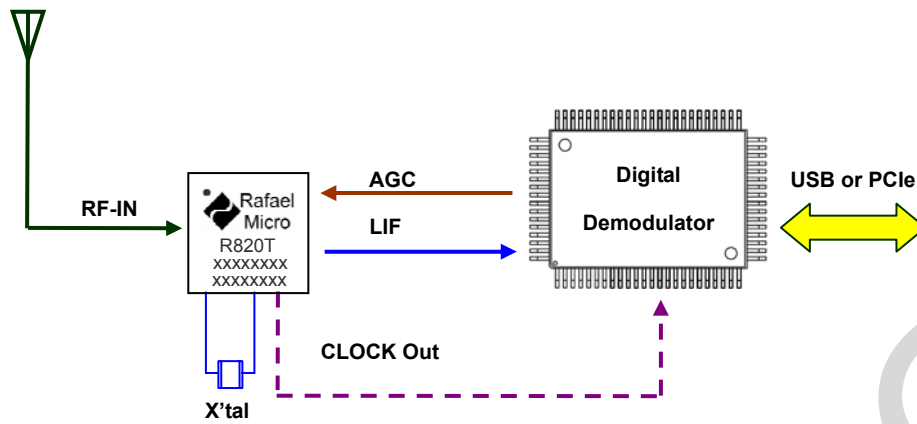


Figure B: Example of Set Top Box Applications

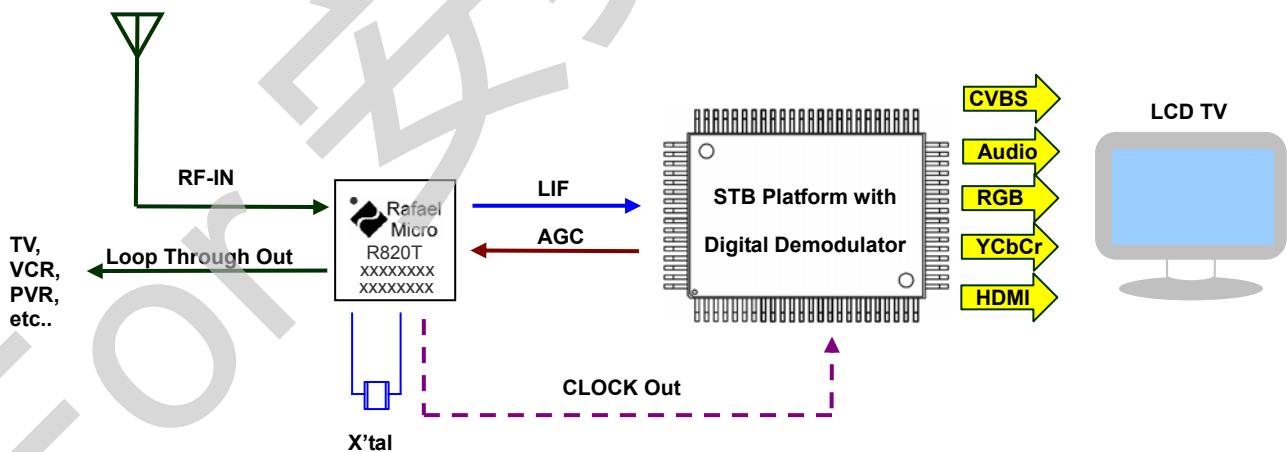
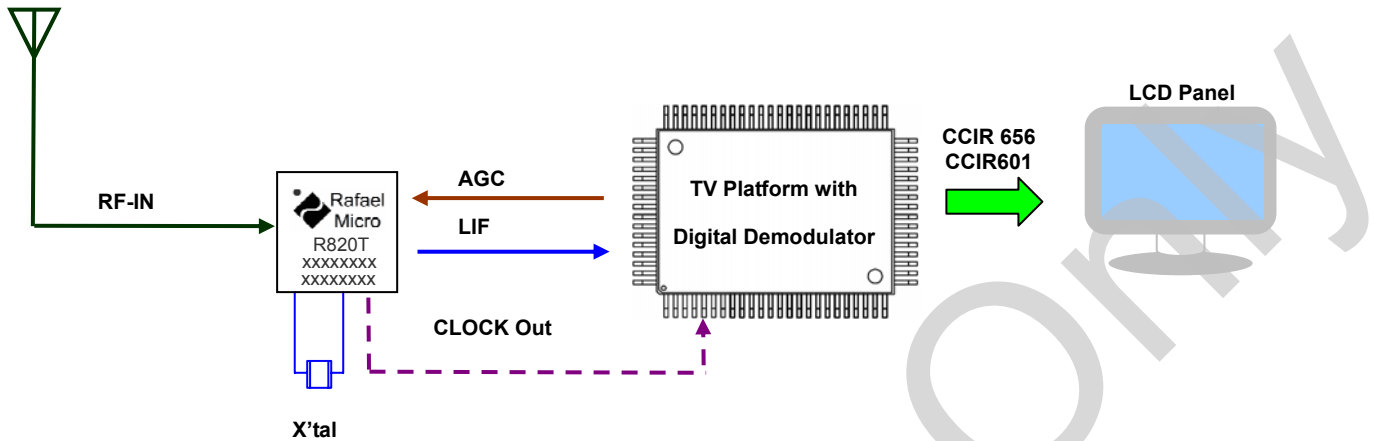


Figure C: Example of LCD TV Applications



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1 Electrical Parameters

1.1 DC Parameters

Table 1-1 : Electrical DC Parameters

Parameters	Condition	Units	Min	Typical	Max
VCC Input voltage		V	3.0	3.3	3.6
Operation Temperature		°C	-20	25	85
Sleeping Mode Current	LT OFF	mA		9	
Standby Mode Current	LT ON	mA		64	
Total Current Consumption	After Programming	mA		178	195

1.2 AC Parameters

Table 1-2 : Electrical AC Parameters

Parameters	Condition	Units	Min	Typical	Max
Input Return Loss ¹	S11	dB		-10	
Operation Frequency Range		MHz	42		1002
Voltage Gain		dB	85		95
AGC Range		dB		104	
Noise Figure	@ Max Gain	dB		3.5	
IIP3	LNA Max Gain	dBm		-7.5	
	LNA Min Gain	dBm		+35	
Image Rejection		dBc		65	
Phase Noise	1K	dBc		-91	
	10K	dBc		-98	
	100K	dBc		-109	
CSO	110 Channel at 75dBuV	dBc		-67	
CTB		dBc		-65	
Multiple Crystal Frequency Spurious	Refer to RF-In	dBm		-120	
RF in to Loop through gain ¹		dB		0	
Loop through Return loss ¹		dB		-13	
Sensitivity	FFT:8k,QPSK,CR:1/2	dBm		-97.5	
	FFT:8k,16QAM,CR:1/2	dBm		-91.5	
	FFT:8k,64QAM,CR:3/4	dBm		-81.5	
Adjacent Channel Rejection	FFT:8k,64QAM,CR:7/8	dBm		-79.5	
	Analog Interference at DVB-T Signal	dBc		-47	
Max. Input Power	FFT:8k,64QAM,CR:7/8	dBm		+10	
IF Output Level	Swing	Vp-p		1	2
	Impedence		Differential 2kΩ//5pF		
PLL Locking time		ms			5

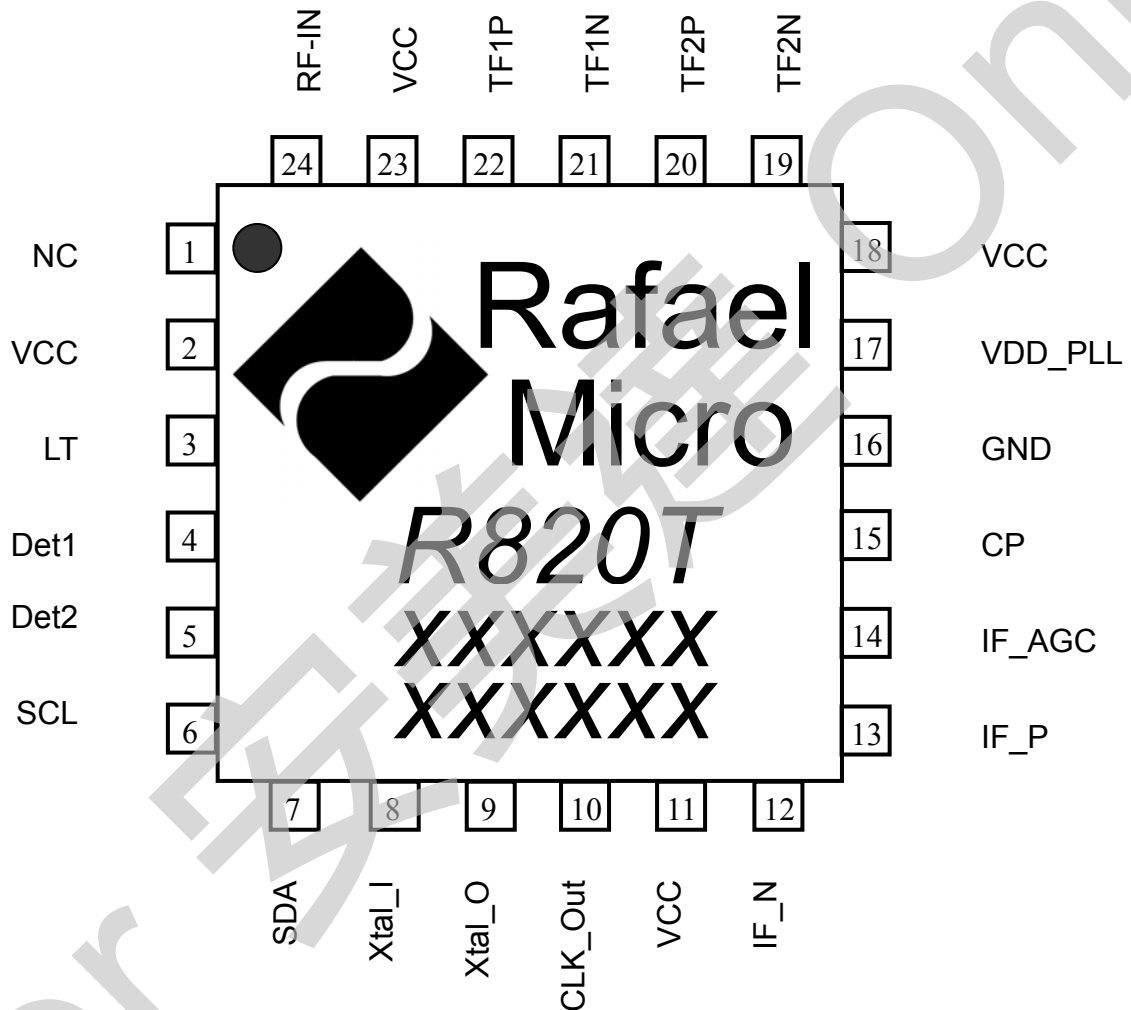
Notes:

1. Network Analyzer Measurement Power : -20dBm

2 Pin Description

Pin Allocation

Figure 2-1 : Pin Allocation (note: E-Pad is GND)



Pin Assignment

Table 2-1 : Summary List of Pin Assignment

Pin Number	Symbol	Description
24	RF_In	RF Input
1	NC	Not Connect
2,11,18,23	VCC	Tuner 3.3V voltage input
3	LT	Loop through output
4,5	Detx	Power detector decoupling capacitor
6	SCL	I2C bus, clock input
7	SDA	I2C bus, data input/ output
8	Xtal_I	Crystal oscillator Input
9	Xtal_O	Crystal oscillator Output
10	CLK_Out	Clock output for sharing Crystal oscillator
12	IF_N	IF output
13	IF_P	IF output
14	IF_AGC	IF automatic gain control input
15	CP	PLL charge pump
17	VDD_PLL	PLL 2V supply output decoupling
19,20,21,22	TFxx	Tracking filter, the detail as Figure 2-1: Pin Allocation.
16	GND	Ground
0	GND	Exposed pad

3 Programming and Registers

3.1 I²C Series Programming Interface

The programmable features of the R820T are accessible through an I²C compatible serial interface. Bi-directional data transfers are programmed through the serial clock (SCL) and serial data lines (SDA) at a standard clock rate of 100 KHz and up to 400KHz.

Data Transfer Logic

The I²C control byte includes a fixed 7-bit slave address ID and a read/write (R/W) bit. Fixed I²C slave address ID 0011010 (0x1A) is used for default setting. The R/W bit is set 0 for write and 1 for read (Table 3-1). Write mode and read mode will be further explained in the following sections.

I²C Write/Read Address

Table 3-1 : I²C Read / Write Address

I ² C Mode	I ² C Address(Bin)							R/W	Address (Hex)
	MSB							LSB	
Write Mode	0	0	1	1	0	1	0	0	0x34
Read Mode	0	0	1	1	0	1	0	1	0x35

Write Mode

When the slave address matches the I²C device ID with write control bit, I²C start interprets the following first byte as first written register address. These following bytes are all the register data (page write I²C control). Register 0 to Register 4 are reserved for internal use only and can be written by I²C write command.

Figure 3-1 : The Typical Write Mode Sequence

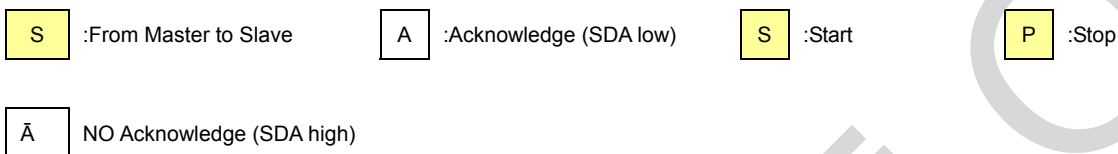
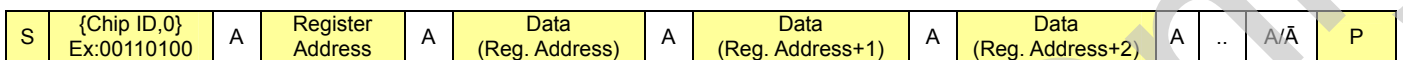
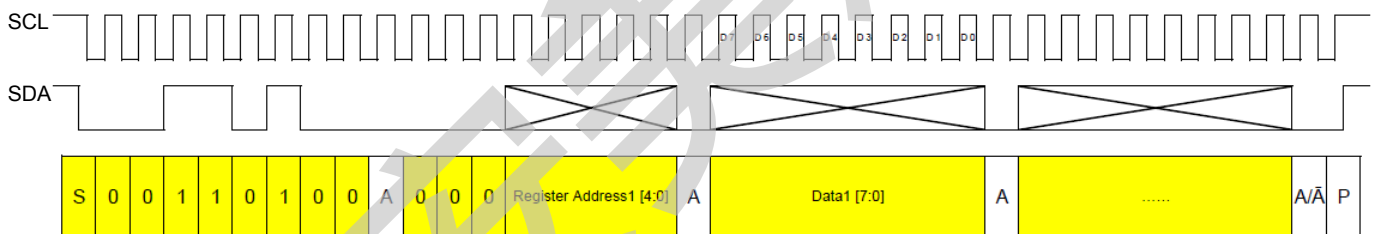


Figure 3-2 : An Example of Write Mode Procedure



Read Mode

When the slave address matches the I²C device ID with read control bit, data are immediately transferred after ack command. Reading data transmission begins from core register 0 to final register until “P”(STOP) occurs. The data is transmitted from LSB to MSB, and the data of register 0 (0x96) is fixed as reference check point for read mode.

Figure 3-3 : The Typical Read Mode Sequence

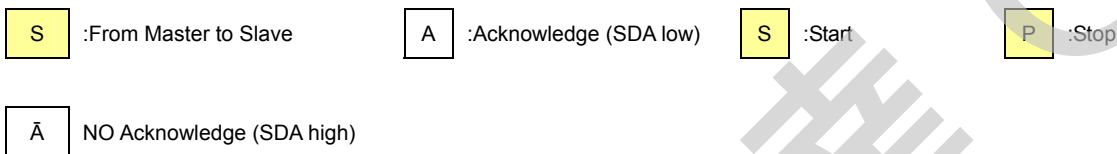
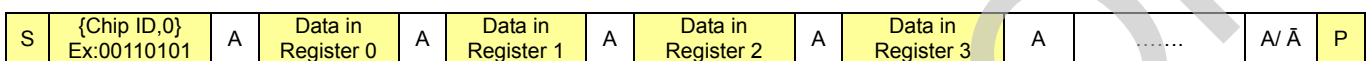
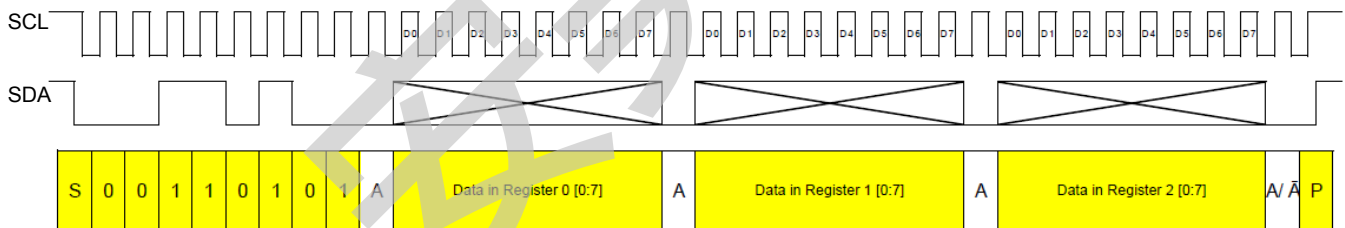


Figure 3-4 : An Example of Read Mode Procedure



Inductance Spec							
Inductance	Tolerance	Q Min.	@ 100MHz	@ 300MHz	@ 500MHz	S.R.F Min	Max. DCI
8n2H	0.5±0.15	≥8	≥10	≥27	≥30	3600MHz	0.4Q
100nH	0.5±0.15	≥8	≥10	≥12	-	700MHz	2.6Q
150nH	0.5±0.15	≥8	≥10	-	-	550MHz	3.2Q
180nH	0.5±0.15	≥8	≥10	-	-	500MHz	3.7Q

4.2 Application Notes

Please contact Rafael Micro Application Engineering for the detailed layout application note. The following guidelines together with proper implementation should be considered in board level layout to achieve the best performance.

1. To improve ESD/EOS reliability, RF input port and I2C bus needs an ESD protection circuit.
2. Minimize the RF trace from RF connector to device RF input pin..
3. RF traces should be protected with ground traces and guard rings.
4. Shielded connectors should be used with all shields connected to the ground plane with low impedance connections.
5. Minimize the ground path to device E-pad for the crystal.
6. Place crystal should be far away from RF traces.
7. Crystal traces should be protected with ground traces and guard rings.
8. The crystal amplifier oscillator has a dedicated power supply pin (Pin11), which should be carefully decoupled to ground with minimal lead lengths in order to minimize board noise from coupling into the reference clock.
9. System clocks and frequently switched signals should not be routed close to the crystal and RF trace.
10. Place AGC filter and CP filter circuits as close to the device as possible.
11. Minimize the CP filter ground path to device E-pad.
12. System digital traces should be routed away from RF traces.
13. Place ceramic DC bypass capacitors as close to the device as possible. This will insure that the power goes through the capacitors before power goes through the VIAs to the power plane
14. If possible power and ground should be on separate dedicated layers.

4.3 IF Frequency

R820T receives RF signal and feed through internal low-noise amplifier, power detector, band-pass filter, and image rejection filter. The mixer down-converts the RF signal to a low-IF frequency, which depends on channel bandwidth in different applications. The standard IF filters are implemented for 6/7/8 MHz channel bandwidths.

Table 4-1 : IF Frequency Table

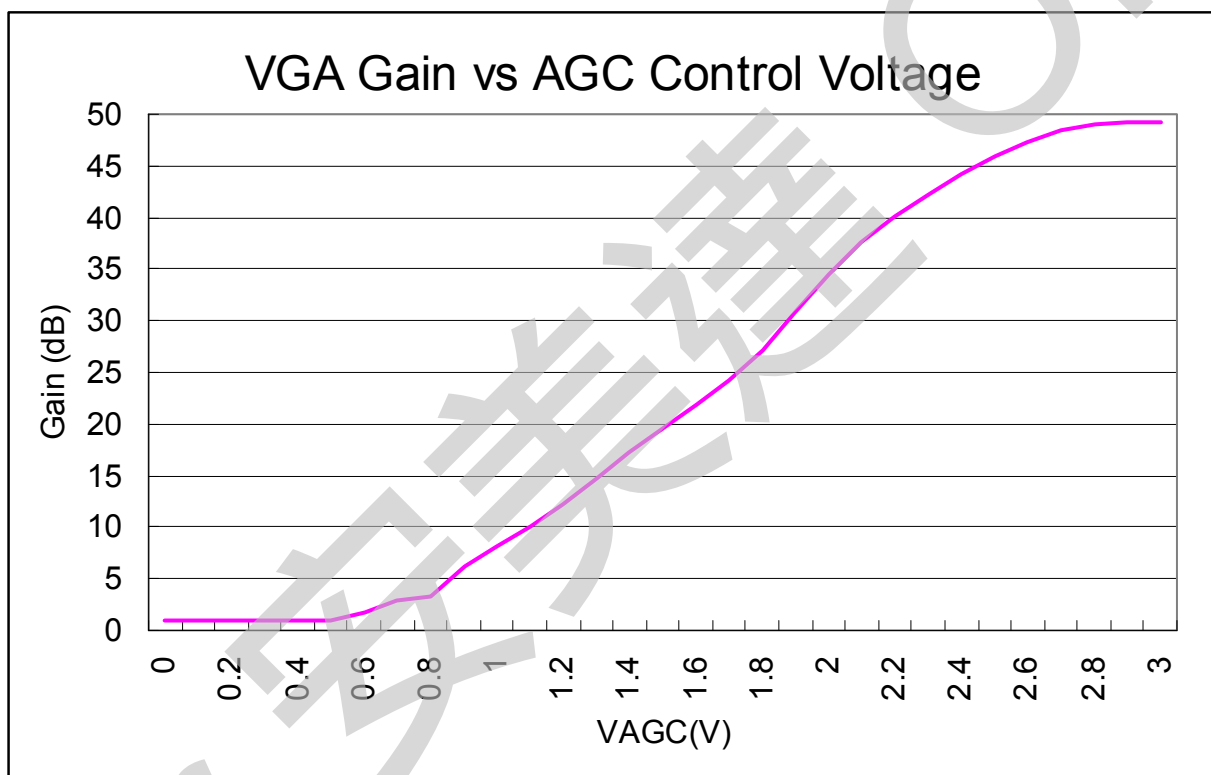
	TV Standard	Channel BW	Center Frequency
1	ATSC (Digital)	BW = 6MHz	Fcenter= 4.063MHz
2	DVB-T (Digital)	BW = 6MHz	Fcenter= 3.57MHz
3	DVB-T (Digital)	BW = 7MHz	Fcenter= 4.07MHz
4	DVB-T (Digital)	BW = 7MHz	Fcenter= 4.57MHz
5	DVB-T (Digital)	BW = 8MHz	Fcenter= 4.57MHz
7	ISDB-T (Digital)	BW = 6MHz	Fcenter = 4.063MHz
8	DTMB (Digital)	BW = 8MHz	Fcenter = 4.57MHz

4.4 AGC Control

The R820T has built-in RFAGC to achieve the optimal SNR while minimizing distortion. When RF input power increases, the internal power detector is activated to attenuate internal LNA gain in an optimal level. On another hand, when RF input power decreases, internal power detector will increase internal LNA gain to achieve good picture quality.

The IFVGA control is available for the demodulator to control the gain of output VGA. R820T provides a wide range of IFVGA gain from +1dB to +48dB. Demodulator AGC output voltage range from 0.6V to 2.5V.

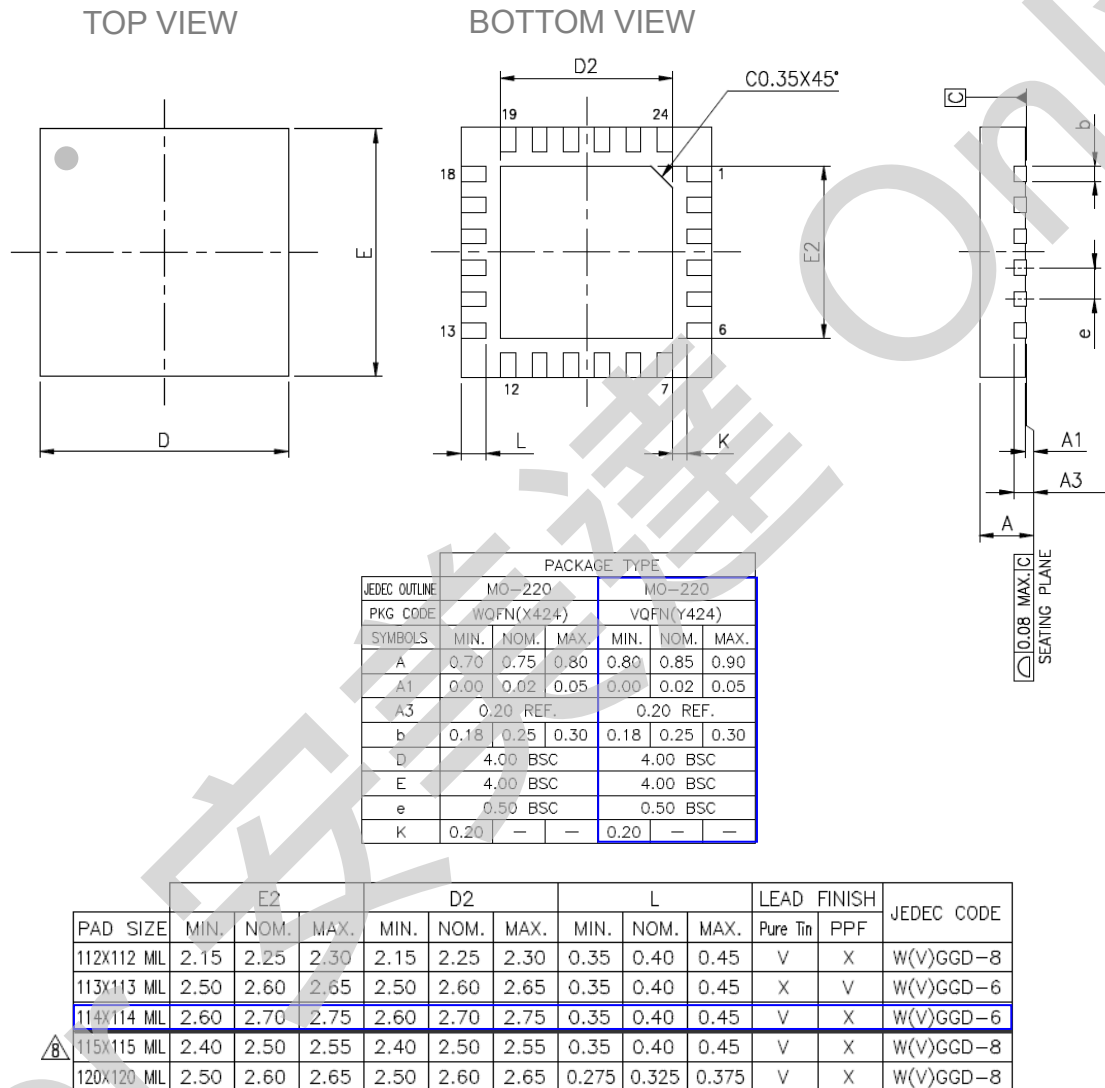
Figure 4-2 : VGA Gain vs AGC control Voltage



5 Package Dimensions and Outline

The R820T is packaged by a Lead-Free 4x4 24-pin Quad Flat No-Lead (QFN) package. The detail package dimensions are listed in Figure 5-1.

Figure 5-1 : Package Dimensions and Outline



Note:

Before soldering to system board, R820T need to be baked at 125°C for more than 8 hours to eliminate moisture contamination.

6 Crystal Requirements

6.1 Crystal Specifications

The default crystal frequency for R820T is 16 MHz. The R820T is well accompanied with traditional DIP package crystal. To reduce component count and foot factor, a low profile SMD package crystal is recommended. Please contact Rafael Micro application engineering for other crystal frequencies (12, 20, 20.48, 24, 27, 28.8, 32 MHz) applications.

Table 6-1 : Crystal Specifications

Parameter	Min	Typical	Max	Units
Frequency Range		16		MHz
ESR			50	Ω
Frequency accuracy		± 30	± 50	ppm
Load Capacitor (CL)		16		pF
Input level to XTAL_P pin when using external clock	120		3300	mVp-p

6.2 Clock Output Swing

The R820T clock output swing is programmable through I2C interface. The IC provides a clock output signal in triangle waveform with output voltage typical at 2.0Vp-p. The output voltage specification assumes an off-chip load impedance of 16pF/ 10M Ω .

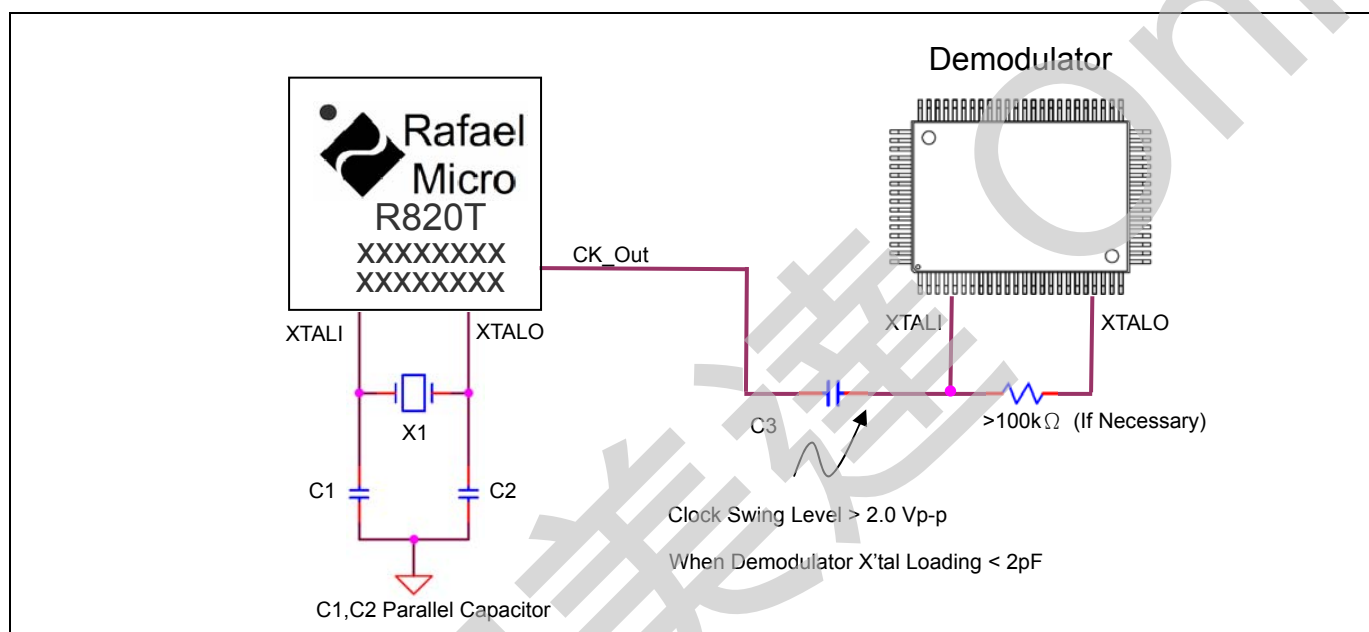
Table 6-2 : Clock Output Specifications

Parameter	Min	Typical	Max	Units
Clock Output Swing (16pF // 10M Ω)		2.0		Vp-p

6.3 Crystal Parallel Capacitors and Share Crystal

Crystal parallel capacitors are recommended when a default crystal frequency of 16 MHz is implemented. Please contact Rafael Micro application engineering for crystal parallel capacitors using other crystal frequencies. For cost sensitive project, the R820T can share crystal with backend demodulators or baseband ICs to reduce component count. The recommended reference design for crystal loading capacitors and share crystal is shown as below.

Figure 6-1 : Crystal Parallel Capacitors and Share Crystal



Note:

Crystal X1=16MHz/ CL=16pF

Bypass capacitor C3=10nF

Crystal parallel capacitors C1=C2=27pF

7 Hardware Tolerance Specifications

To achieve better RF performance, hardware tolerance for tracking filter inductors and RF input inductors is highly recommended in the R820T reference design..

Table 7-1 : Value and specification of Tracking filter inductors and RF input inductors
(Reference Figure 4-1: Reference Application Schematic)

Reference	L (nH)	Tolerance	Q Min.	L, Q test frequency	Q at 100 MHz	Q at 300 MHz	Q at 500 MHz	S.R.F. Min.	DCR Max.
L3,	180	0.5 +/- 0.15	8	100 MHz	10	-	-	500 MHz	3.7 ohm
L7	100	0.5 +/- 0.15	8	100 MHz	10	12	-	700 MHz	2.6 ohm
L2,L6	150	0.5 +/- 0.15	8	100 MHz	10	-	-	550 MHz	3.2 ohm
L9	8.2	0.5 +/- 0.15	8	100 MHz	10	27	30	3600MHz	0.4 ohm



R320T

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